	Туре	L #	Hits	Search Text	DBs	Time Stamp
	BRS	L1	168	(silicon adj oxide) near10 [(etch adj stop adj layer)		2002/07/29 15:29
2	BRS	L2	4	(silicon adj oxide) near10 (organosilicate)	JSPAT; JS-PGP JB; EPO; JPO; DERWEN T; IBM_TD B	
3	BRS	L4	1	1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TI	2002/07/29
4	BRS	L 5	35913	silicon adj oxide	USPAT	2002/07/29 15:34
5	BRS	L6	129	5 near5 (etch adj stop adj layer)	USPAT	2002/07/29 15:43
6	BRS	L7	6932	(etch or etching) near10 (silicon adj oxide)	USPAT	2002/07/29
7	BRS	L8	2	7 same (organosilicate)	USPAT	2002/07/29 16:43
8	BRS	L9	2	(organosilicate) near10 (etch or etching or etched	USPAT	10.40
9	BRS	L10	11	organosilicate near10 temperature	USPAT	2002/07/29 16:50
10		L11	175	(silicon adj oxide) near10 (etch or etched or etching near10 pressure) USPAT	
	1 BRS	L12	31	11 same temperature	USPAT	2002/07/29 16:51